

ABSTRACT OF THE DISCLOSURE

An arrangement having p-doped semiconductor layers and n-doped semiconductor layers which exhibits transitions between the p-doped semiconductor layers and n-doped semiconductor layers, the transitions displaying a Zener breakdown upon application of a voltage characteristic of a transition, a plurality of transitions between p-doped semiconductor layers and n-doped semiconductor layers being present, and the characteristic voltages additively make up the breakdown voltage of the entire arrangement. Also described is a method for manufacturing the arrangement.